## CLAIMS:

- A semiconductor device comprising:
   a semiconductor substrate;
   a gate line crossing over the semiconductor substrate; and
   a protecting pattern covering ends of the gate line.
  - 2. The semiconductor device of claim 1, wherein the protecting pattern is formed of a material chosen from the group consisting of silicon nitride and silicon oxide.
  - 3. The semiconductor device of claim 1, further comprising a spacer covering sidewalls of the gate line and interposed between the gate line and the protecting pattern at the ends of the gate line.
- 15 4. The semiconductor device of claim 3, wherein the spacer is formed of a material chosen from the group consisting of silicon nitride and silicon oxide.
- The semiconductor device of claim 1, wherein the gate line comprises an oxide pattern and a conductive pattern that are sequentially stacked on the semiconductor
   substrate.
  - 6. The semiconductor device of claim 5, wherein the conductive pattern is formed of a metal selected from the group consisting of tungsten, copper, and aluminum.
- 7. A method of forming a semiconductor device, comprising:
  forming a gate line at a semiconductor substrate;
  forming a spacer covering sidewalls of the gate line; and
  forming a protecting pattern covering ends of the gate line.
- 30 8. The method of claim 7, wherein forming a spacer and forming a protecting pattern comprises forming the spacer and forming the protecting pattern simultaneously, wherein the spacer and the protecting pattern are formed of a same material.

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- 9. The method of claim 8, wherein the same material is chosen from the group consisting of silicon nitride and silicon oxide.
- The method of claim 7, wherein forming the gate line comprises:
   sequentially stacking an oxide layer and a conductive layer on the semiconductor substrate; and

sequentially patterning the conductive layer and the oxide layer.

11. The method of claim 10, wherein the conductive layer is formed of a metal selected from the group consisting of tungsten, copper, and aluminum.